

NDF06N60Z

Power MOSFET, N-Channel, 600 V, 1.2 Ω

Features

- Low ON Resistance
- Low Gate Charge
- ESD Diode-Protected Gate
- 100% Avalanche Tested
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Rating	Symbol	Value	Unit
Drain-to-Source Voltage	V_{DSS}	600	V
Continuous Drain Current, $R_{\theta JC}$ (Note 1)	I_D	7.1	A
Continuous Drain Current $T_A = 100^\circ\text{C}$, $R_{\theta JC}$ (Note 1)	I_D	4.5	A
Pulsed Drain Current, $V_{GS} @ 10\text{ V}$	I_{DM}	28	A
Power Dissipation, $R_{\theta JC}$	P_D	35	W
Gate-to-Source Voltage	V_{GS}	± 30	V
Single Pulse Avalanche Energy, $L = 6.3\text{ mH}$, $I_D = 6.0\text{ A}$	E_{AS}	113	mJ
ESD (HBM) (JESD22-A114)	V_{esd}	3000	V
RMS Isolation Voltage ($t = 0.3\text{ sec.}$, $R.H. \leq 30\%$, $T_A = 25^\circ\text{C}$) (Figure 13)	V_{ISO}	4500	V
Peak Diode Recovery (Note 2)	dv/dt	4.5	V/ns
MOSFET dV/dt	dV/dt	60	V/ns
Continuous Source Current (Body Diode)	I_S	6.0	A
Maximum Temperature for Soldering Leads	T_L	260	$^\circ\text{C}$
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to 150	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

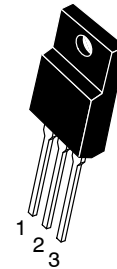
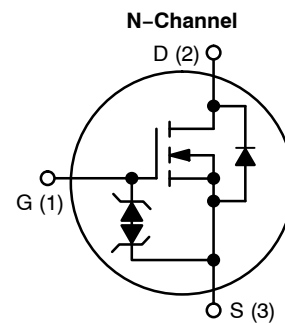
1. Limited by maximum junction temperature
2. $I_{SD} = 6.0\text{ A}$, $di/dt \leq 100\text{ A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, $T_J = +150^\circ\text{C}$



ON Semiconductor®

www.onsemi.com

$V_{DSS} (@ T_{Jmax})$	$R_{DS(ON)} (MAX) @ 3\text{ A}$
650 V	1.2 Ω



NDF06N60ZG,
NDF06N60ZH
TO-220FP
CASE 221AH

ORDERING AND MARKING INFORMATION

See detailed ordering, marking and shipping information on page 6 of this data sheet.

NDF06N60Z

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction-to-Case (Drain)	$R_{\theta JC}$	3.6	°C/W
Junction-to-Ambient Steady State (Note 3)	$R_{\theta JA}$	50	

3. Insertion mounted

Electrical Characteristics (T_J = 25°C unless otherwise noted)

Characteristic	Test Conditions	Symbol	Min	Typ	Max	Unit
----------------	-----------------	--------	-----	-----	-----	------

OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	V _{GS} = 0 V, I _D = 1 mA	BV _{DSS}	600			V
Breakdown Voltage Temperature Co-efficient	Reference to 25°C, I _D = 1 mA	$\Delta BV_{DSS} / \Delta T_J$		0.6		V/°C
Drain-to-Source Leakage Current	V _{DS} = 600 V, V _{GS} = 0 V	I _{DSS}	25°C		1	μA
			150°C		50	
Gate-to-Source Forward Leakage	V _{GS} = ±20 V	I _{GSS}			±10	μA

ON CHARACTERISTICS (Note 4)

Static Drain-to-Source On-Resistance	V _{GS} = 10 V, I _D = 3.0 A	R _{DS(on)}		0.98	1.2	Ω
Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 100 μA	V _{GS(th)}	3.0	3.9	4.5	V
Forward Transconductance	V _{DS} = 15 V, I _D = 3.0 A	g _{FS}		5.0		S

DYNAMIC CHARACTERISTICS

Input Capacitance (Note 5)	V _{DS} = 25 V, V _{GS} = 0 V, f = 1.0 MHz	C _{iss}	738	923	1107	pF
Output Capacitance (Note 5)		C _{oss}	90	106	125	
Reverse Transfer Capacitance (Note 5)		C _{rss}	15	23	30	
Total Gate Charge (Note 5)	V _{DD} = 300 V, I _D = 6.0 A, V _{GS} = 10 V	Q _g	15.5	31	47	nC
Gate-to-Source Charge (Note 5)		Q _{gs}	3	6.3	9.5	
Gate-to-Drain ("Miller") Charge (Note 5)		Q _{gd}	8	17	24.5	
Plateau Voltage		V _{GP}		6.4		V
Gate Resistance		R _g		3.2		Ω

RESISTIVE SWITCHING CHARACTERISTICS

Turn-On Delay Time	V _{DD} = 300 V, I _D = 6.0 A, V _{GS} = 10 V, R _G = 5 Ω	t _{d(on)}		13		ns
Rise Time		t _r		17		
Turn-Off Delay Time		t _{d(off)}		30		
Fall Time		t _f		28		

SOURCE-DRAIN DIODE CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Diode Forward Voltage	I _S = 6.0 A, V _{GS} = 0 V	V _{SD}			1.6	V
Reverse Recovery Time	V _{GS} = 0 V, V _{DD} = 30 V I _S = 6.0 A, di/dt = 100 A/μs	t _{rr}		338		ns
Reverse Recovery Charge		Q _{rr}		2.0		μC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Pulse Width ≤ 380 μs, Duty Cycle ≤ 2%.

5. Guaranteed by design.

TYPICAL CHARACTERISTICS

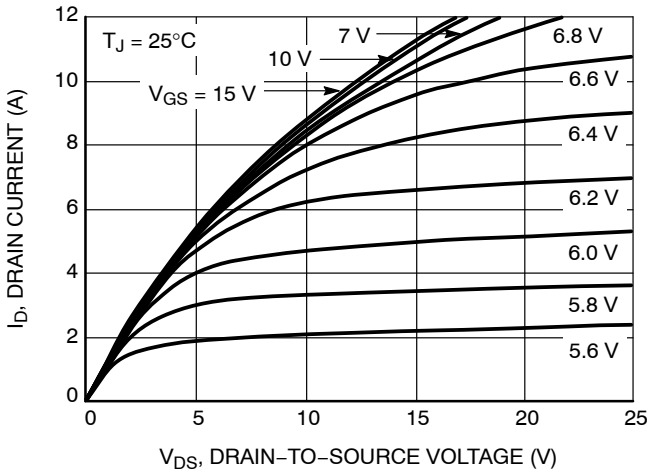


Figure 1. On-Region Characteristics

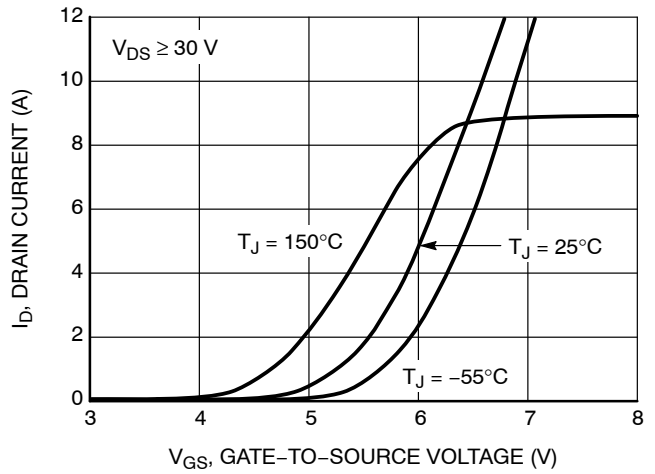


Figure 2. Transfer Characteristics

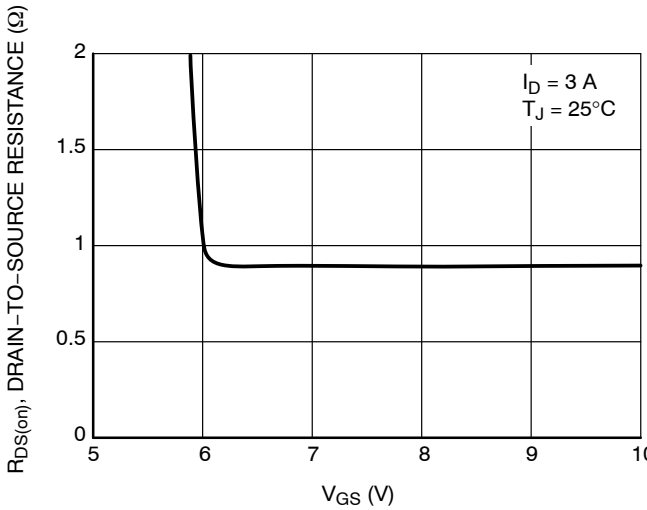


Figure 3. On-Resistance vs. V_{GS}

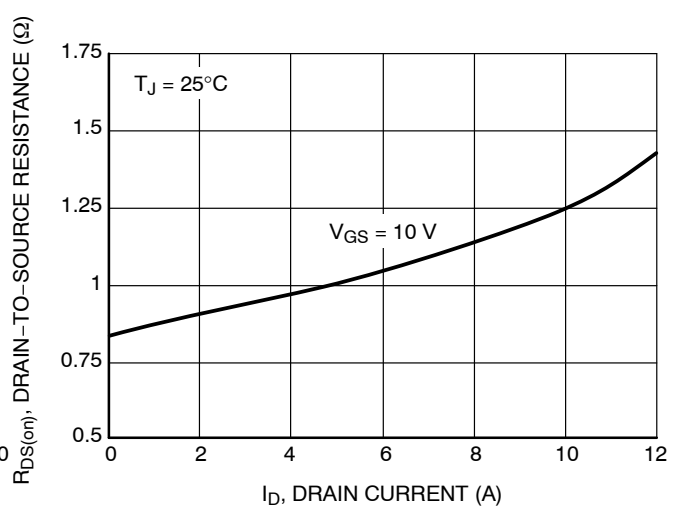


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

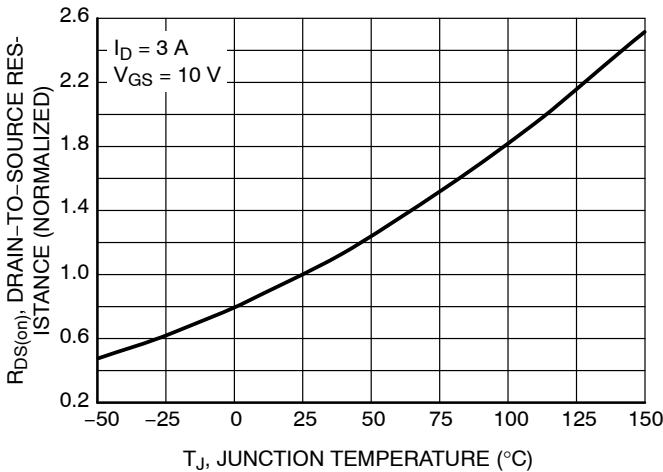


Figure 5. On-Resistance Variation with Temperature

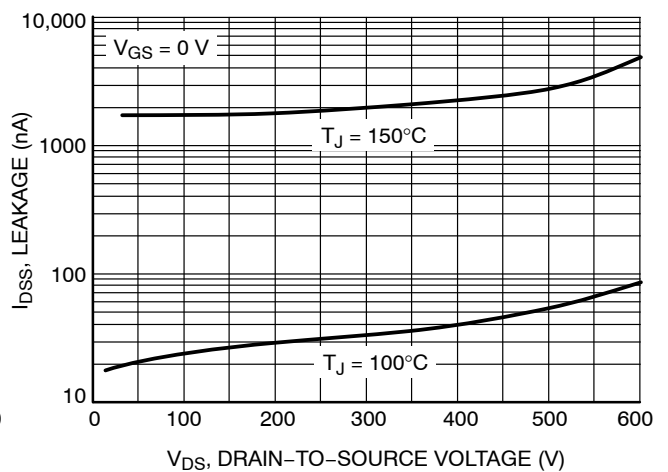


Figure 6. Drain-to-Source Leakage Current vs. Voltage

NDF06N60Z

TYPICAL CHARACTERISTICS

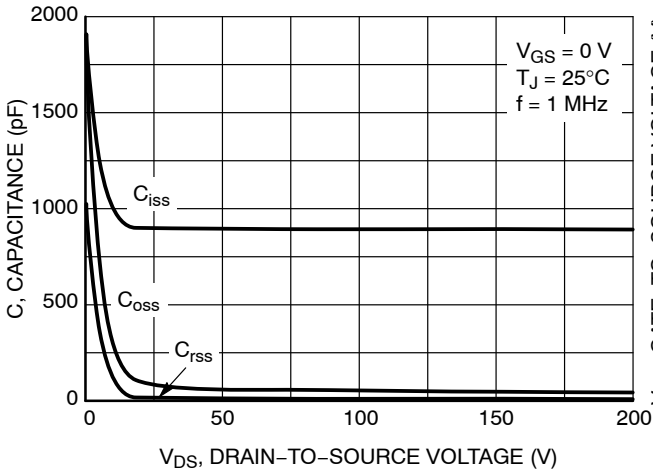


Figure 7. Capacitance Variation

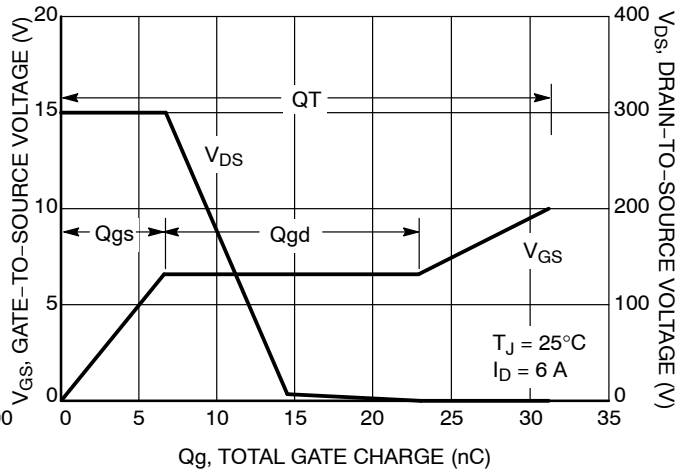


Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

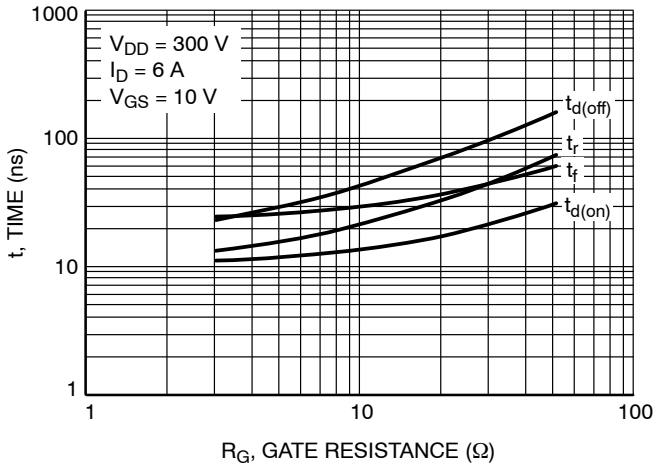


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

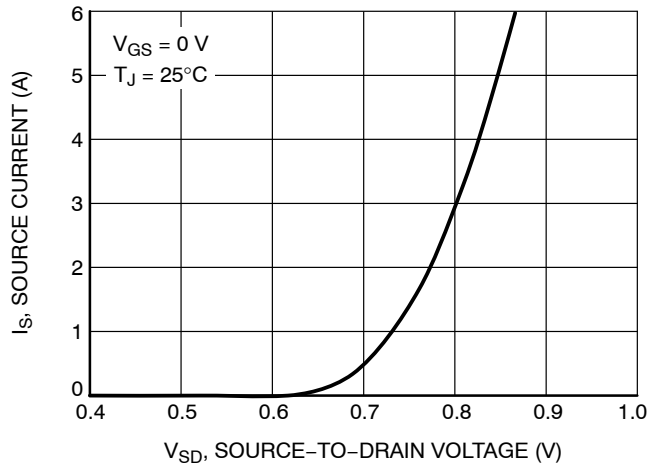


Figure 10. Diode Forward Voltage vs. Current

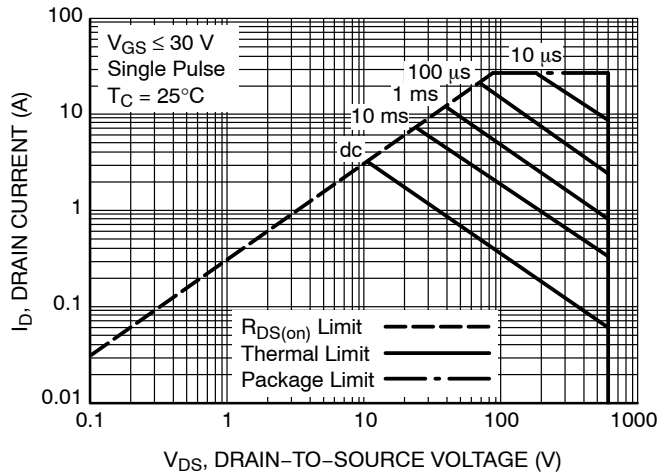


Figure 11. Maximum Rated Forward Biased Safe Operating Area for NDF06N60Z

NDF06N60Z

TYPICAL CHARACTERISTICS

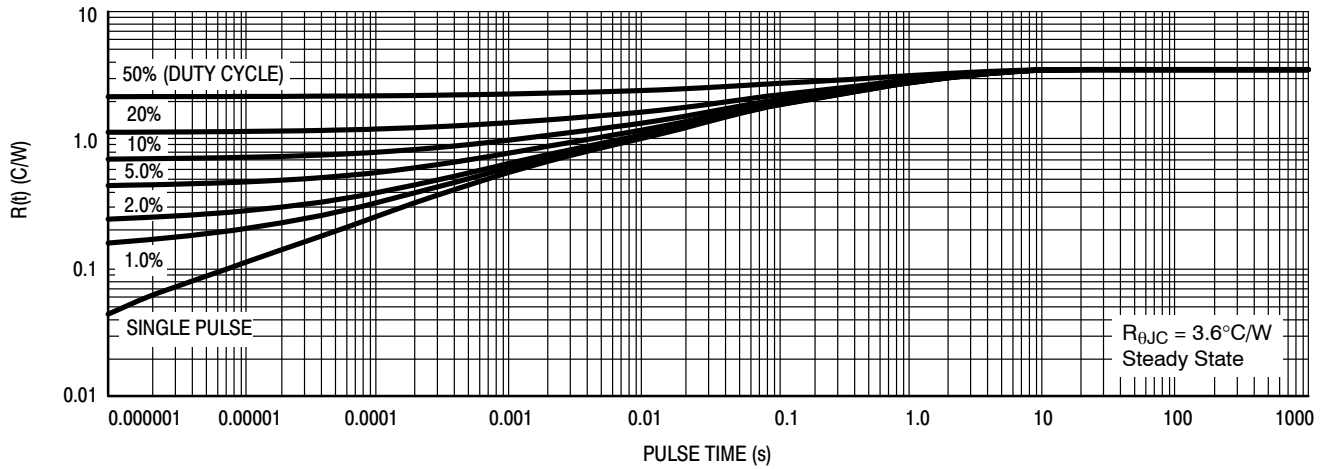


Figure 12. Thermal Impedance for NDF06N60Z

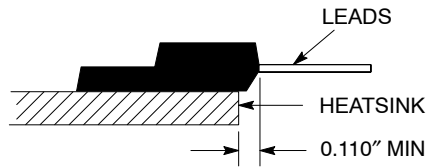


Figure 13. Mounting Position for Isolation Test

Measurement made between leads and heatsink with all leads shorted together.

*For additional mounting information, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

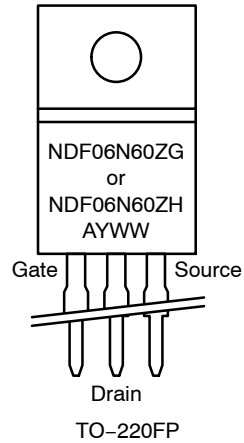
NDF06N60Z

ORDERING INFORMATION

Order Number	Package	Shipping†
NDF06N60ZG	TO-220FP (Pb-Free, Halogen-Free)	50 Units / Rail
NDF06N60ZH	TO-220FP (Pb-Free, Halogen-Free)	50 Units / Rail

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MARKING DIAGRAMS



A = Location Code
Y = Year
WW = Work Week
G, H = Pb-Free, Halogen-Free Package

MECHANICAL CASE OUTLINE

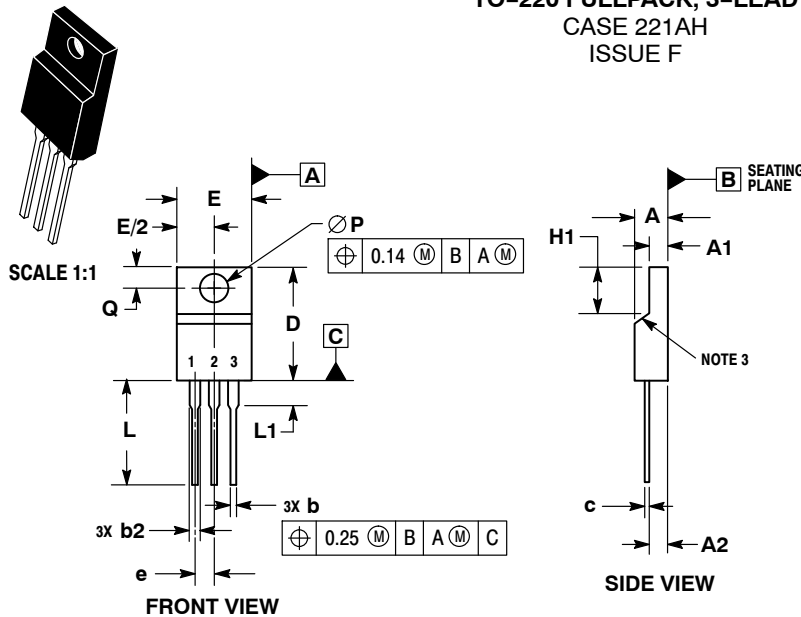
PACKAGE DIMENSIONS

ON Semiconductor®



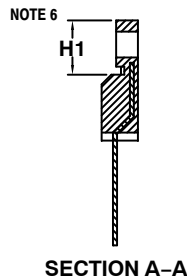
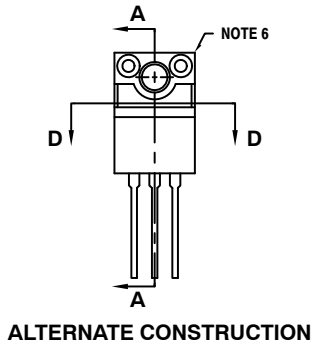
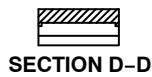
TO-220 FULLPACK, 3-LEAD CASE 221AH ISSUE F

DATE 30 SEP 2014

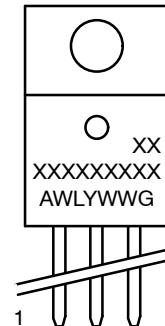


- NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. CONTOUR UNCONTROLLED IN THIS AREA.
 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH AND GATE PROTRUSIONS. MOLD FLASH AND GATE PROTRUSIONS NOT TO EXCEED 0.13 PER SIDE. THESE DIMENSIONS ARE TO BE MEASURED AT OUTERMOST EXTREME OF THE PLASTIC BODY.
 5. DIMENSION b2 DOES NOT INCLUDE DAMBAR PROTRUSION. LEAD WIDTH INCLUDING PROTRUSION SHALL NOT EXCEED 2.00.
 6. CONTOURS AND FEATURES OF THE MOLDED PACKAGE BODY MAY VARY WITHIN THE ENVELOPE DEFINED BY DIMENSIONS A1 AND H1 FOR MANUFACTURING PURPOSES.

MILLIMETERS		
DIM	MIN	MAX
A	4.30	4.70
A1	2.50	2.90
A2	2.50	2.90
b	0.54	0.84
b2	1.10	1.40
c	0.49	0.79
D	14.70	15.30
E	9.70	10.30
e	2.54 BSC	
H1	6.60	7.10
L	12.50	14.73
L1	---	2.80
P	3.00	3.40
Q	2.80	3.20



GENERIC MARKING DIAGRAM*



- A = Assembly Location
- WL = Wafer Lot
- Y = Year
- WW = Work Week
- G = Pb-Free Package

- STYLE 1:
PIN 1. MAIN TERMINAL 1
2. MAIN TERMINAL 2
3. GATE
- STYLE 2:
PIN 1. CATHODE
2. ANODE
3. GATE

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present.

DOCUMENT NUMBER:	98AON52577E	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	TO-220 FULLPACK, 3-LEAD	PAGE 1 OF 1

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

onsemi, **Onsemi**, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi**'s product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Email Requests to: orderlit@onsemi.com

onsemi Website: www.onsemi.com

TECHNICAL SUPPORT

North American Technical Support:

Voice Mail: 1 800-282-9855 Toll Free USA/Canada

Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support:

Phone: 00421 33 790 2910

For additional information, please contact your local Sales Representative